Silicon NPN transistor in a TO-92 Plastic Package.

High f_T, low output capacitance, low base time constant and high gain, excellent noise characteristics.

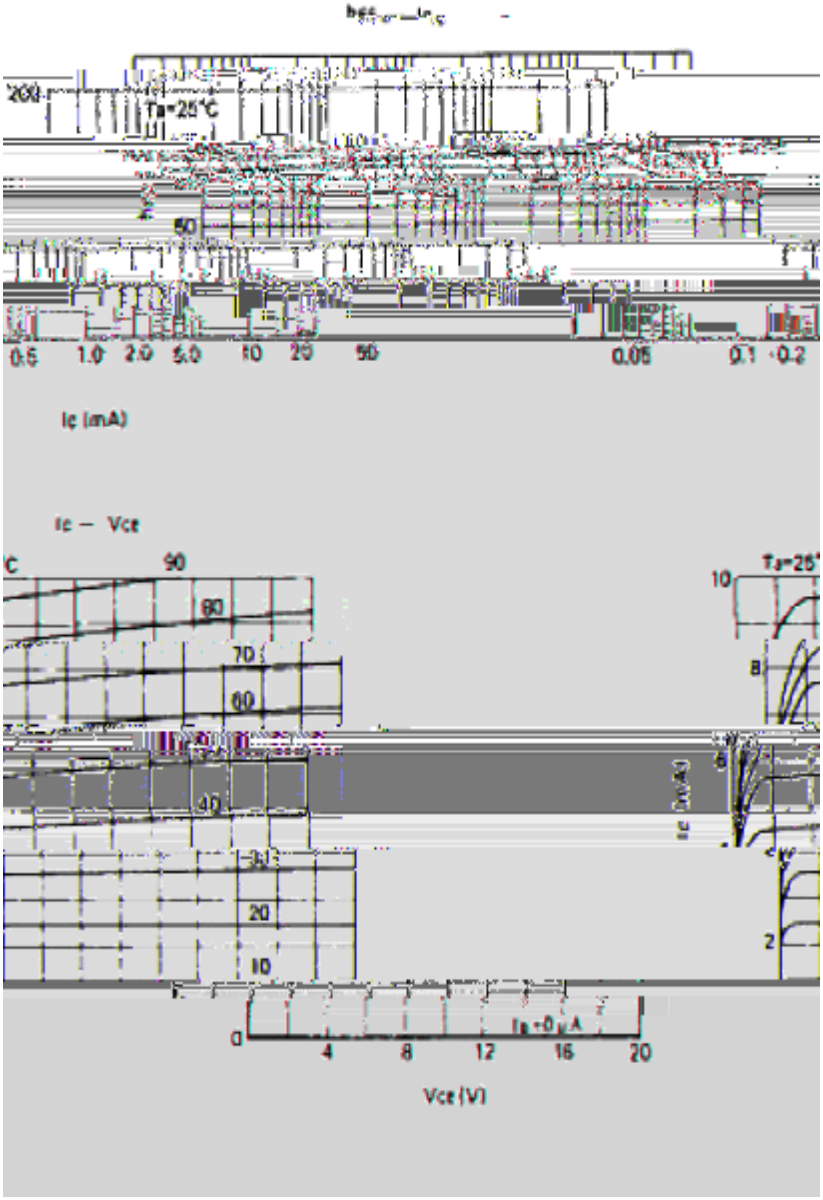
FM radio RF amplifier applications.



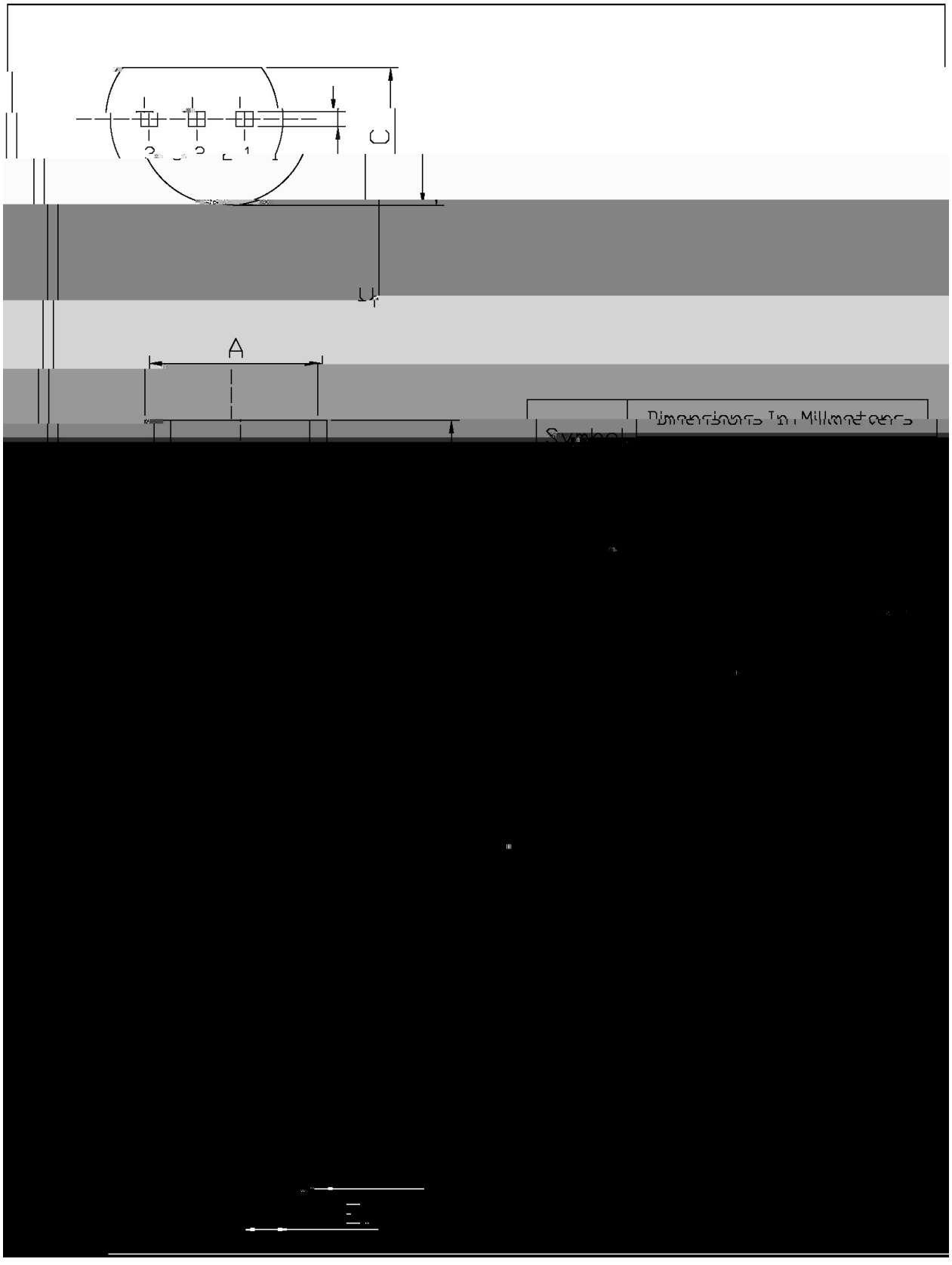
PIN1

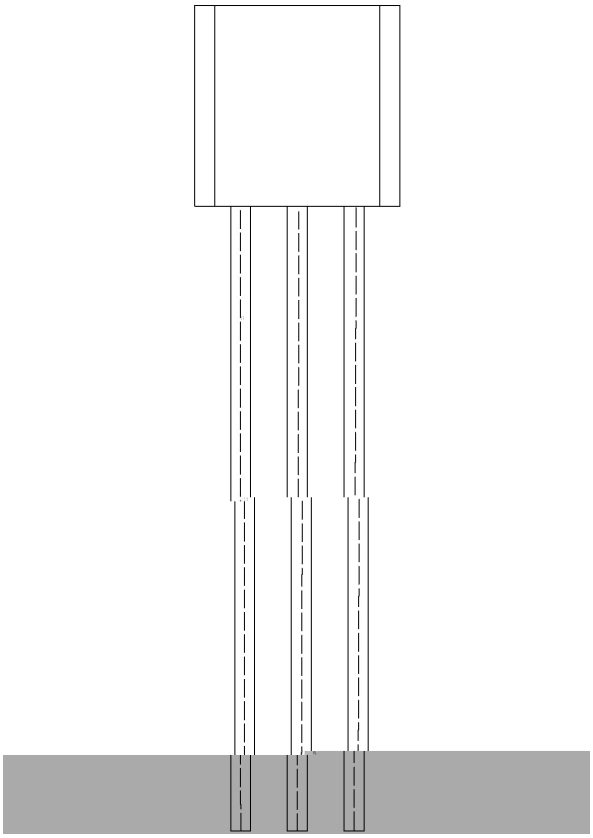
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

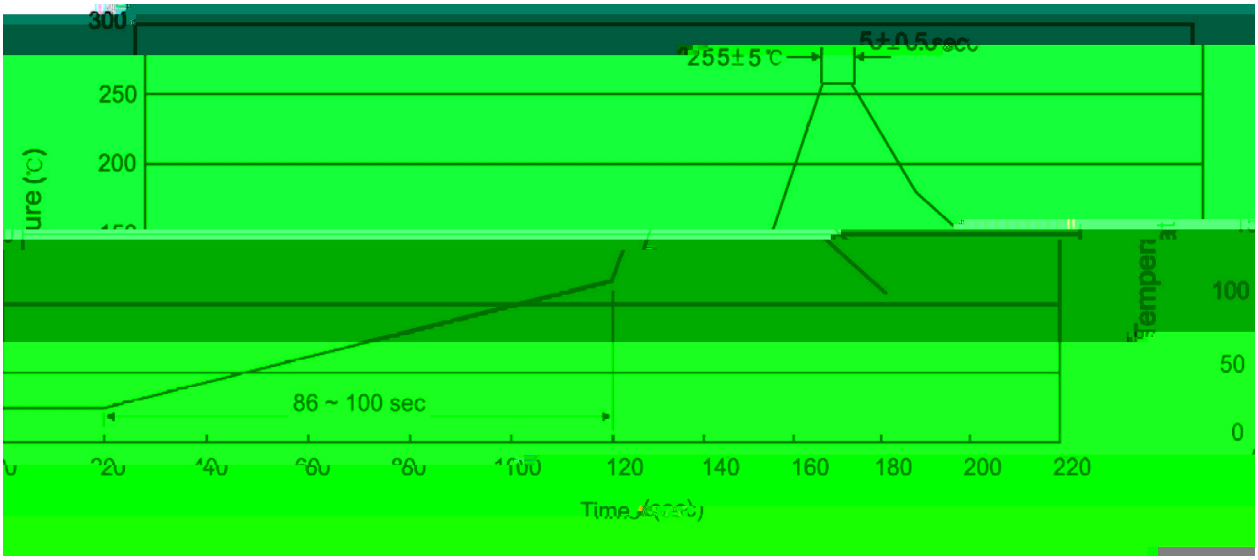
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10 A	25			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10 A	4.0			V


Ta=25°C
200
50
0.5
1.0
2.0
5.0
10
20
50
0.05
0.1
0.2
Ic (mA)
Ic — Vce
90
80
70
60
50
40
30
20
10
0
4
8
12
16
20
Vce (V)
Ta=25°
10
8
6
4
2

TO-92 Unit: mm







	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

270 5 10 1 sec. Temp:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)